

MMST4401

E				
Collector Current -Continuous	IC	mA		600
Total Device Dissipation	PD	mW		200
Junction Temperature	Tj			150
Storage Temperature	TSTG			-55 to +150

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	UNIT WEIGHT(g)	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MMST4401	F2	Approximate 0.005	3000	30000	120000	7" reel



■ **Electrical Characteristics** (Ta=25 unless otherwise noted)

Item	Symbol	Unit	Conditions	Min	Typ	Max
Collector-base breakdown voltage	$V_{(BR)CBO}$	V	IC=10mA, IE=0	60		
Collector-emitter breakdown voltage	$V_{(BR)CEO^*}$	V	IC =1mA, IB=0	40		
Emitter-base breakdown voltage	$V_{(BR)EBO}$	V	IE=100μA, IC=0	6		
Collector-emitter cut-off current	I_{CEO}	nA	VCE=35V, IB=0			100
Collector-base cut-off current	I_{CBO}	nA	VCB=35V, IE =0			100
Emitter-base cut-off current	I_{EBO}	nA	VEB=5 V, IC =0			100
DC current gain	h_{FE}		VCE=1V, IC=150mA	100		300
			VCE=2V, IC=500mA	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	V	IC=150mA, IB=15mA			0.4
Base-emitter saturation voltage	$V_{BE(sat)}$	V	IC=150mA, IB=15mA			0.95
Transition frequency	f_T	MHz	VCE=10V, IC=20mA, f=100MHz	250		
Delay time	t_d	ns	VCC=30V, VBE(off)=0.2V IC=150uA, IB1=15mA			15
Rise time	t_r	ns				20
Storage time	t_s	ns	VCC=30V, IC=150mA, IB1=IB2=15mA			225
Fall time	t_f	ns				60
Output Capacitance	C_{ob}	pF	VCB=10V, IE=0 f=1MHz			6.5



■ Characteristics (Typical)



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